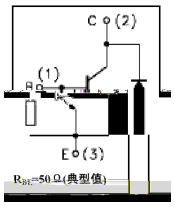
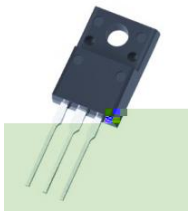
Silicon NPN transistor in a TO-220F Plastic Package.

High breakdown voltage, Low drain current, High switching speed, Low saturation voltage, Excellent current characteristics.

Color TV Horizontal deflection output applications.





PIN1 Base PIN 2 Collector PIN 3 Emitter

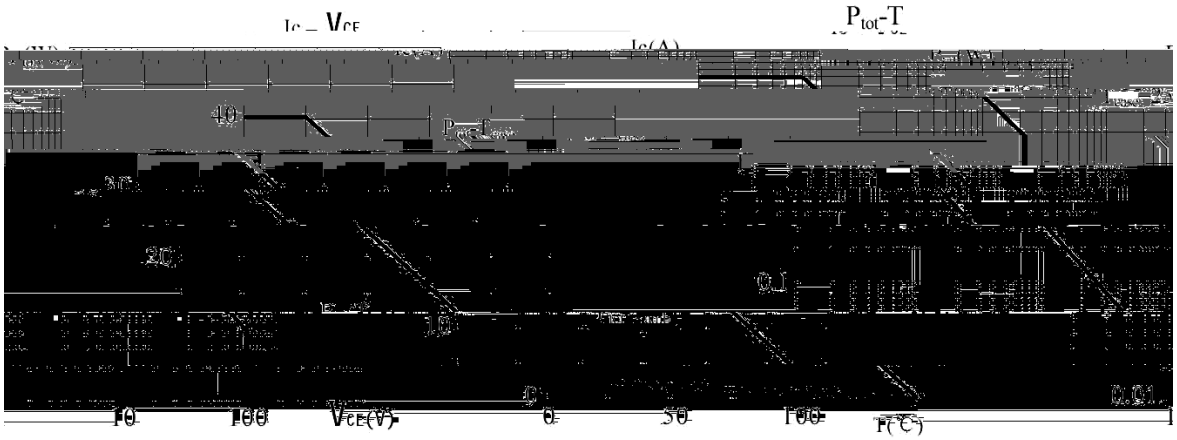
/ h_{FE} Classifications & Marking

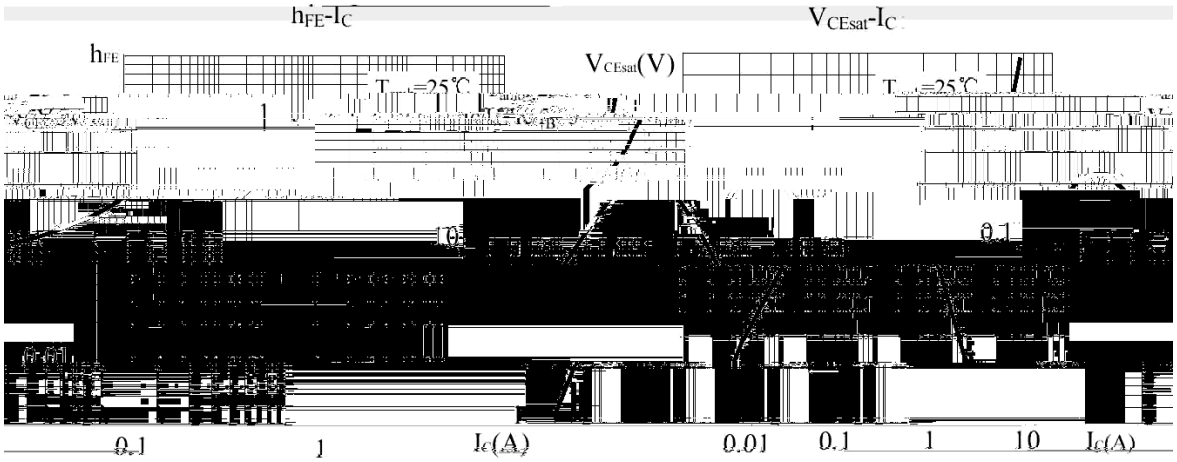
See Marking Instructions.

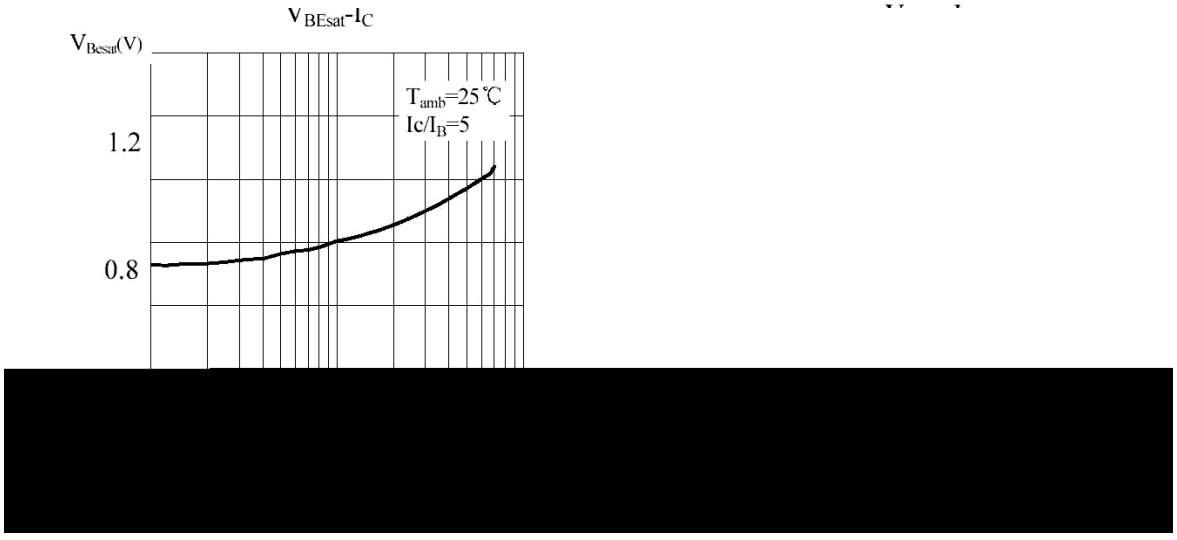
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	6.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=25)	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=1500V I_E=0			1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0	40		200	mA
DC Current Gain*	h_{FE}*	V_{CE}=5.0V I_C=1.0A	10		40	
Collector to Emitter Saturation Voltage*	$V_{CE(sat)}$*	I_C=4.0A I_B=1.0A			5.0	V
Base to Emitter Saturation Voltage*	$V_{BE(sat)}$*	I_C=4.0A I_B=1.0A			1.5	V
Fall Time	t_f	V_{CC}=100V I_C=5.0A $2I_{B1}$=-I_{B2}=1.0A			1.0	s
Transition Frequency	f_T	V_{CE}=10V I_C=0.1A f=0.3MHz	=10V			

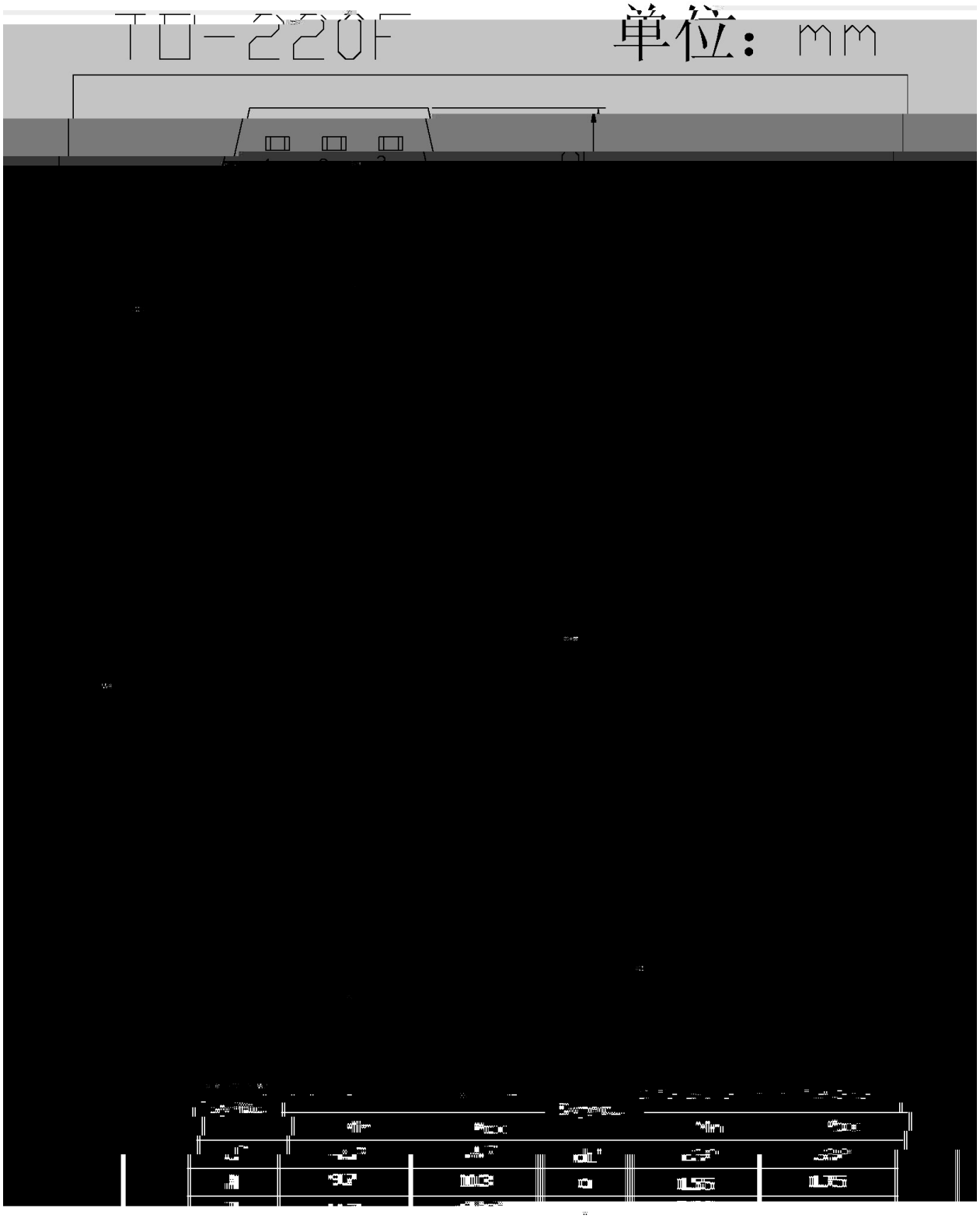
/ Electrical Characteristic Curve



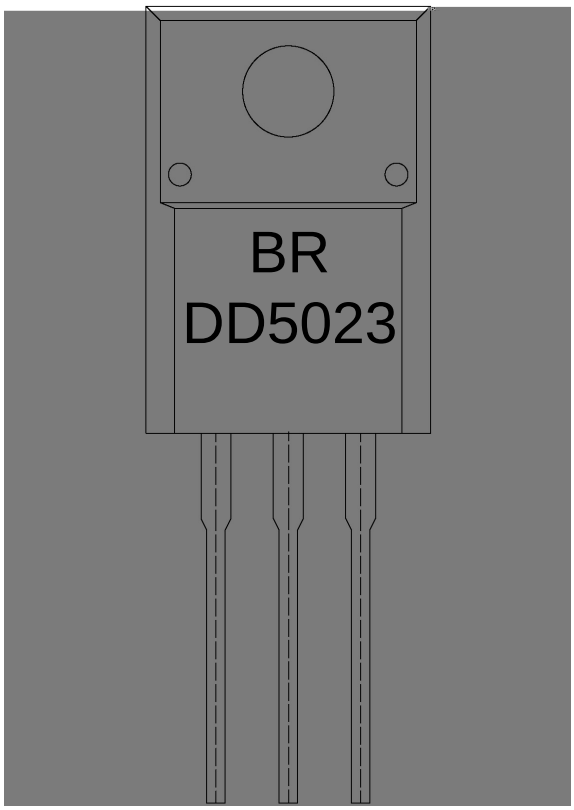




/ Package Dimensions



/ Marking Instructions



Note:

BR:	Company Code.
DD5023:	Product Type.
****:	Lot No. Code, code change with Lot No.

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